

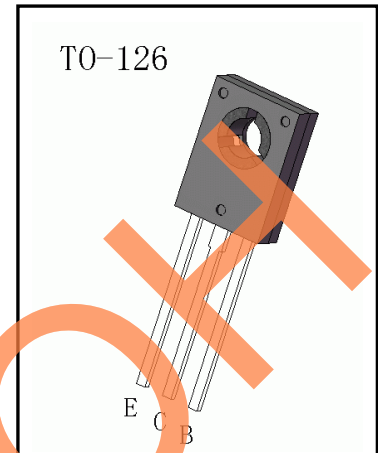
BD140 NPN transistor

Package type: TO-126

Pin arrangement: E C B

Limit parameters (absolute maximum rated value Ta=25°C)

Parameter name	symbol	parameter values	unit
collector-base voltage	BVCBO	40	V
collector-emitter voltage	BVCEO	30	V
emitter-base voltage	BVEBO	5	V
maximum collector current	ICM	1.5	A
dissipated power	PCM	2	W
storage temperature	Tj、Tstg	-55 ~ + 150	°C



Electrical parameters (Ta=25°C)

Parameter name	symbol	test condition	parameter values			unit
			least value	representative value	crest value	
collector-base voltage	BVCBO	IC = 100μA, IE = 0	40			V
collector-emitter voltage	BVCEO	IC = 100μA, IB = 0	30			V
emitter-base voltage	BVEBO	IE = 100μA, IC = 0	5			V
collector-base leakage current	ICBO	VCB = 40V, IE = 0			0.1	μA
collector-emitter leakage current	ICEO	VCE = 30V, IB = 0			0.1	μA
emitter-base drain current	IEBO	VEB = 5V, IC = 0			0.1	μA
DC gain	HFE	VCE = 5V, IB = 1mA	160		350	
		VCE = 5V, IB = 5mA	160		350	
saturated pressure drop	VCESAT	IC = 2A, IB = 200mA			0.5	
forward voltage drop	VBESAT	IC = 2A, IB = 200mA			2	V
characteristic frequency	fT	VCE = 5V, IB = 100mA		90		MHZ

HFE (1) standard grading

bracket				
scope	160-350			

TPMA TPOH